

Silicon NPN Power Transistors

2SD716

DESCRIPTION

- With TO-3P(I) package
- Complement to type 2SB686

APPLICATIONS

- Power amplifier applications
- Recommend for 30~35W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

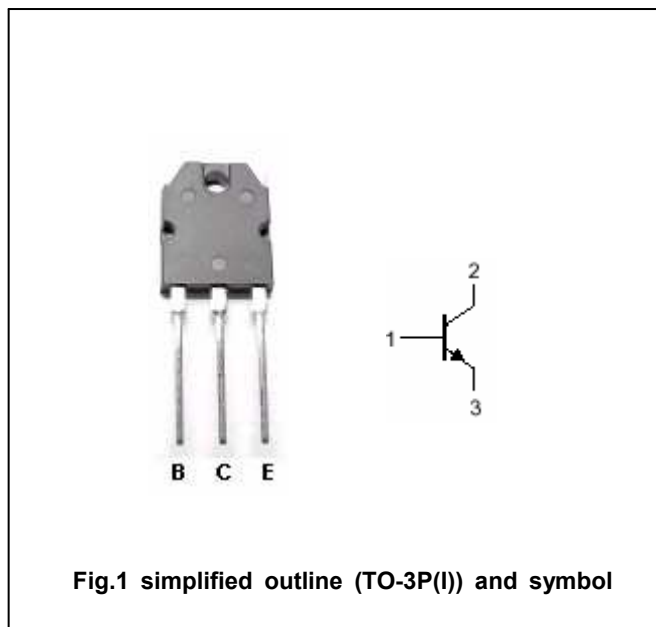


Fig.1 simplified outline (TO-3P(I)) and symbol

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_E	Emitter current		-6	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	60	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA, I _B =0	100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA, I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4A			2.0	V
V _{BE}	Base-emitter voltage	I _C =4A; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =1A; V _{CE} =5V	55		160	
f _T	Transition frequency	I _C =1A; V _{CE} =5V		12		MHz
C _{ob}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		100		pF

◆ h_{FE} Classifications

R	O
55-110	80-160

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PACKAGE OUTLINE

